MJL4281A (NPN) MJL4302A (PNP)

Preferred Device

Complementary NPN-PNP Silicon Power Bipolar Transistors

The MJL4281A and MJL4302A are PowerBase[™] power transistors for high power audio.

Features

- 350 V Collector–Emitter Sustaining Voltage
- Gain Complementary:
 - Gain Linearity from 100 mA to 5 A High Gain - 80 to 240
 - $h_{FE} = 50 \text{ (min)} @ I_C = 8 \text{ A}$
- Low Harmonic Distortion
- High Safe Operation Area 1.0 A/100 V @ 1 Second
- High f_T
- Pb-Free Packages are Available*

MAXIMUM RATINGS (T_{.1} = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|--|-----------------------------------|-------------|-----------|
| Collector-Emitter Voltage | V _{CEO} | 350 | Vdc |
| Collector-Base Voltage | V _{CBO} | 350 | Vdc |
| Emitter-Base Voltage | V _{EBO} | 5.0 | Vdc |
| Collector-Emitter Voltage - 1.5 V | V _{CEX} | 350 | Vdc |
| Collector Current – Continuous – Peak (Note 1) | Ι _C | 15 30 | Adc |
| Base Current – Continuous | Ι _Β | 1.5 | Adc |
| Total Power Dissipation @ T _C = 25°C Derate Above 25°C | PD | 230 1.84 | W ∘C/W |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -65 to +150 | °C |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--------------------------------------|-----------------|------|------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 0.54 | °C/W |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

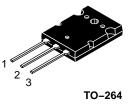
1. Pulse Test: Pulse Width = 5 ms, Duty Cycle < 10%.



ON Semiconductor®

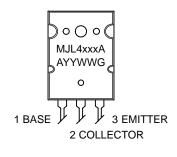
http://onsemi.com

15 AMPERES COMPLEMENTARY SILICON POWER TRANSISTORS 350 VOLTS, 230 WATTS



CASE 340G **STYLE 2**

MARKING DIAGRAM



| ххх | = 281 or 302 |
|-----|---------------------|
| А | = Assembly Location |
| ΥY | = Year |
| WW | = Work Week |
| G | = Pb-Free Package |

ORDERING INFORMATION

| Device | Package | Shipping |
|-----------|---------------------|---------------|
| MJL4281A | TO-264 | 25 Units/Rail |
| MJL4281AG | TO–264 (Pb–Free) | 25 Units/Rail |
| MJL4302A | TO-264 | 25 Units/Rail |
| MJL4302AG | TO–264 (Pb–Free) | 25 Units/Rail |

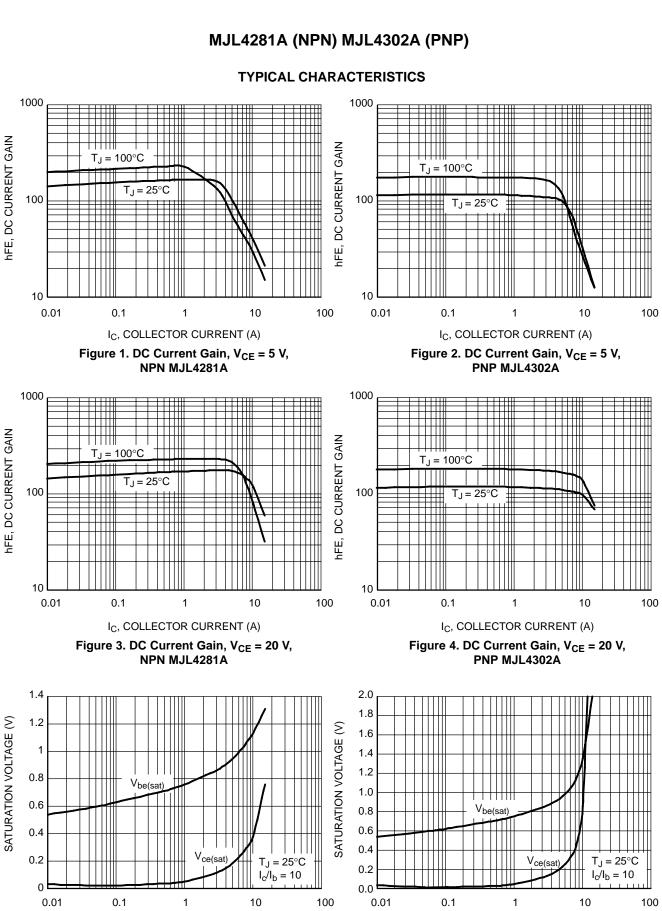
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.

MJL4281A (NPN) MJL4302A (PNP)

ELECTRICAL CHARACTERISTICS (T_C = 25° C unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|--|----------------------|----------------------------------|------------------------------------|------|
| OFF CHARACTERISTICS | | | | |
| Collector Emitter Sustaining Voltage $(I_C = 50 \text{ mA}, I_B = 0)$ | V _{CE(sus)} | 350 | | Vdc |
| Collector Cut-off Current ($V_{CE} = 200 \text{ V}, I_B = 0$) | I _{CEO} | | 100 | μAdc |
| Collector Cutoff Current ($V_{CB} = 350$ Vdc, $I_E = 0$) | I _{CBO} | _ | 50 | μAdc |
| Emitter Cutoff Current ($V_{EB} = 5.0 \text{ Vdc}, I_C = 0$) | I _{EBO} | _ | 5.0 | μAdc |
| SECOND BREAKDOWN | | | | |
| Second Breakdown Collector with Base Forward Biased $(V_{CE} = 50 \text{ Vdc}, t = 1.0 \text{ s} (\text{non-repetitive})$ $(V_{CE} = 100 \text{ Vdc}, t = 1.0 \text{ s} (\text{non-repetitive})$ | I _{S/b} | 4.5 1.0 | | Adc |
| ON CHARACTERISTICS | | | | |
| $ \begin{array}{l} \text{DC Current Gain} \\ (I_{C} = 100 \text{ mAdc}, \text{V}_{CE} = 5.0 \text{ Vdc}) \\ (I_{C} = 1.0 \text{ Adc}, \text{V}_{CE} = 5.0 \text{ Vdc}) \\ (I_{C} = 3.0 \text{ Adc}, \text{V}_{CE} = 5.0 \text{ Vdc}) \\ (I_{C} = 5.0 \text{ Adc}, \text{V}_{CE} = 5.0 \text{ Vdc}) \\ (I_{C} = 8.0 \text{ Adc}, \text{V}_{CE} = 5.0 \text{ Vdc}) \\ (I_{C} = 15 \text{ Adc}, \text{V}_{CE} = 5.0 \text{ Vdc}) \\ (I_{C} = 15 \text{ Adc}, \text{V}_{CE} = 5.0 \text{ Vdc}) \end{array} $ | h _{FE} | 80 80 80 80 50 10 | 250 250 250 250 - - | _ |
| Collector–Emitter Saturation Voltage $(I_C = 8.0 \text{ Adc}, I_B = 0.8 \text{ Adc})$ | V _{CE(sat)} | _ | 1.0 | Vdc |
| Emitter–Base Saturation Voltage $(I_C = 8.0 \text{ Adc}, I_B = 0.8 \text{ A})$ | V _{BE(sat)} | _ | 1.4 | Vdc |
| Base–Emitter ON Voltage $(I_C = 8.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc})$ | V _{BE(on)} | _ | 1.5 | Vdc |
| DYNAMIC CHARACTERISTICS | | | | • |
| Current–Gain – Bandwidth Product ($I_C = 1.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc}, f_{test} = 1.0 \text{ MHz}$) | f _T | 35 | _ | MHz |
| Output Capacitance (V_{CB} = 10 Vdc, I _E = 0, f _{test} = 1.0 MHz) | C _{ob} | _ | 600 | pF |



http://onsemi.com 3

I_C, COLLECTOR CURRENT (A)

Figure 6. Typical Saturation Voltage,

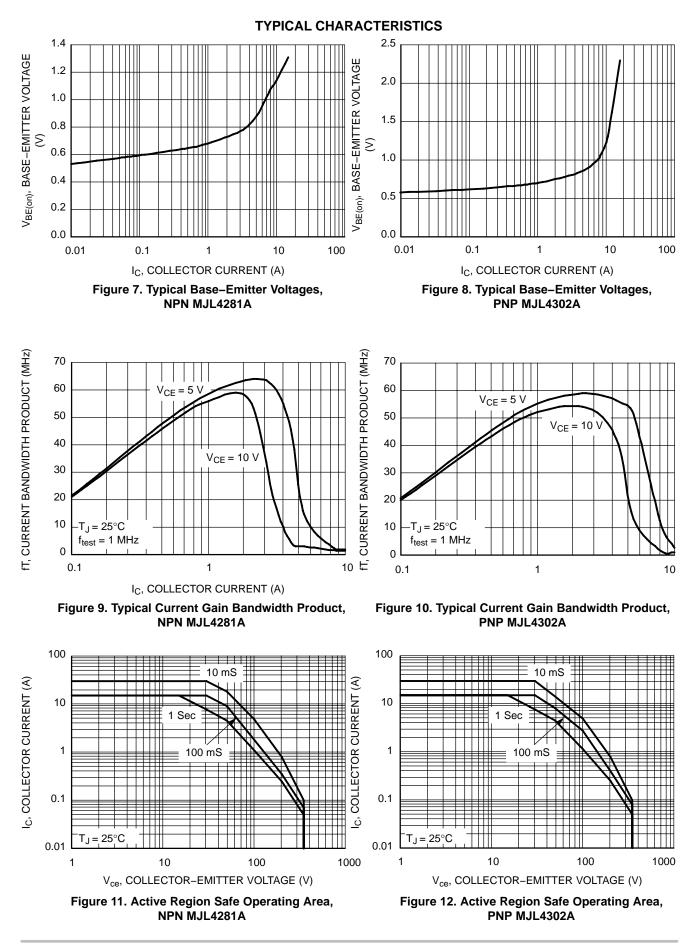
PNP MJL4302A

I_C, COLLECTOR CURRENT (A)

Figure 5. Typical Saturation Voltage,

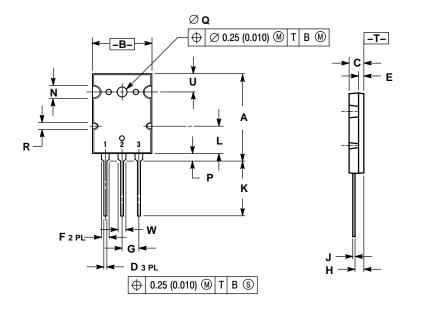
NPN MJL4281A

MJL4281A (NPN) MJL4302A (PNP)



PACKAGE DIMENSIONS

TO-3BPL (TO-264) CASE 340G-02 ISSUE J



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: MILLIMETER

| DIM A B C D | MIN 28.0 19.3 | MAX 29.0 | MIN | MAX |
|-------------------------|---------------------|-------------|-----------|-------|
| B C | | 29.0 | | |
| С | 19.3 | | 1.102 | 1.142 |
| | | 20.3 | 0.760 | 0.800 |
| D | 4.7 | 5.3 | 0.185 | 0.209 |
| | 0.93 | 1.48 | 0.037 | 0.058 |
| E | 1.9 | 2.1 | 0.075 | 0.083 |
| F | 2.2 | 2.4 | 0.087 | 0.102 |
| G | 5.45 BSC | | 0.215 BSC | |
| н | 2.6 | 3.0 | 0.102 | 0.118 |
| J | 0.43 | 0.78 | 0.017 | 0.031 |
| к | 17.6 | 18.8 | 0.693 | 0.740 |
| L | 11.2 REF | | 0.411 REF | |
| Ν | 4.35 REF | | 0.172 REF | |
| Р | 2.2 | 2.6 | 0.087 | 0.102 |
| Q | 3.1 | 3.5 | 0.122 | 0.137 |
| R | 2.25 REF | | 0.089 REF | |
| U | 6.3 REF | | 0.248 REF | |
| w | 2.8 | 3.2 | 0.110 | 0.125 |

STYLE 2: PIN 1. BASE

2. COLLECTOR

3. EMITTER

PowerBase is a trademark of Semiconductor Components Industries, LLC.

ON Semiconductor and IIII are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use persons, and reasonable attorney fees andising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use persons and sensing out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized to applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082–1312 USA Phone: 480–829–7710 or 800–344–3860 Toll Free USA/Canada Fax: 480–829–7709 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2–9–1 Kamimeguro, Meguro–ku, Tokyo, Japan 153–0051 Phone: 81–3–5773–3850 ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.